WHAT IS CLAIMED IS:

1. A blank mask comprising:

a transparent substrate and a light shielding film disposed on the transparent substrate,

wherein the light shielding film comprises a transition metal and at least any one between oxygen and nitrogen, wherein the transition metal comprises chromium,

wherein the light shielding film comprises a first light shielding layer and a second light shielding layer disposed on the first light shielding layer, and

wherein the light shielding film has an Rd value of Equation 1 below which is 0.4 to 0.8;

[Equation 1]

$$Rd = \frac{er_2}{er_1}$$

where in the Equation 1, the er_1 value is an etching rate of the first light shielding layer measured by etching with argon gas, and

the er_2 value is an etching rate of the second light shielding layer measured by etching with argon gas, and

wherein the Do value of Equation 2 below of the light shielding film is less than 0.05;

[Equation 2]

$$Do = Bo - Po$$

where in the Equation 2, the Bo value is an optical density of the light shielding film for a light with a wavelength of 193 nm, and

when a light shielding pattern film formed by patterning the light shielding film is observed at an upper surface, the Po value is an optical density for a light with a wavelength of 193 nm of a measuring area corresponded to an area from an edge of the light shielding pattern

film, to a position spaced apart by 4 mm from the edge in inner side direction of the light shielding pattern film.

2. The blank mask of claim 1,

wherein the er_2 value is 0.4 to 0.5 Å/s.

3. The blank mask of claim 1,

wherein the er_1 value is 0.51 Å/s or more.

4. The blank mask of claim 1,

wherein the transition metal further comprises any one among Ta, Ti and Hf.

5. The blank mask of claim 1,

wherein an etching rate measured with chlorine-based gas of the light shielding film is 1.55 Å/s or more.

6. A blank mask comprising:

a transparent substrate and a light shielding film disposed on the transparent substrate,

wherein the light shielding film comprises a transition metal and at least any one between oxygen and nitrogen, wherein the transition metal comprises chromium,

wherein the light shielding film comprises a first light shielding layer and a second light shielding layer disposed on the first light shielding layer, and

a pattern edge loss area measured from patterning the light shielding film is 10 nm^2 or less;

wherein the pattern edge loss area is an area surrounded a first line, a second line, and a pattern edge profile of patterned light shielding film when TEM (Transmission Electron Microscopy) image of the patterned light shielding film is observed,

wherein the first line is an extended line which links a first point placed at a height of 20 % on a side surface profile of the patterned light shielding film and a second point placed at a height of 40 % on the side surface profile when an entire height of the patterned light shielding film is designated as 100 %,

wherein the second line is an extended line comprising a pattern film crossing point and disposed to be parallel to an upper boundary of the transparent substrate,

wherein the pattern film crossing point is a spot where a pattern film center line and an upper surface profile of the patterned light shielding film meet,

wherein the pattern film center line is an extended line passing through a pattern film center point which is a center point of a lower boundary of the patterned light shielding film, and perpendicular to the upper boundary of the transparent substrate.

7. A photomask comprising a transparent substrate and a light shielding pattern film disposed on the transparent substrate,

wherein the light shielding pattern film comprises a transition metal and at least any one between oxygen and nitrogen, wherein the transition metal comprises chromium,

wherein the light shielding pattern film comprises a first light shielding layer and a second light shielding layer disposed on the first light shielding layer, and

wherein the light shielding pattern film has an Rd value of Equation 1 below which is 0.4 to 0.8;

[Equation 1]

$$Rd = \frac{er_2}{er_1}$$

where in the Equation 1, the er_1 value is an etching rate of the first light shielding layer measured by etching with argon gas, and

the er_2 value is an etching rate of the second light shielding layer measured by etching with argon gas, and

wherein the Do value of Equation 2 below of the light shielding film is less than 0.05;

[Equation 2]

$$Do = Bo - Po$$

where in the Equation 2, the Bo value is an optical density of the light shielding film for a light with a wavelength of 193 nm, and

when a light shielding pattern film formed by patterning the light shielding film is observed at an upper surface, the Po value is an optical density for a light with a wavelength of 193 nm of a measuring area corresponded to an area from an edge of the light shielding pattern film, to a position spaced apart by 4 mm from the edge in inner side direction of the light shielding pattern film.

8. The photomask of claim 7,

wherein a pattern edge loss area of the light shielding pattern film is 10 nm^2 or less.

9. A manufacturing method of a semiconductor element comprises a preparing operation of disposing a light source, a photomask, and a semiconductor wafer where a resist film has been applied, an exposure operation of selectively transmitting a light incident from the light source on the semiconductor wafer through the photomask and a development

operation of developing a pattern on the semiconductor wafer,

wherein the photomask comprises a transparent substrate and a light shielding pattern film disposed on the transparent substrate,

wherein the light shielding pattern film comprises a transition metal and at least any one between oxygen and nitrogen, wherein the transition metal comprises chromium,

wherein the light shielding pattern film comprises a first light shielding layer and a second light shielding layer disposed on the first light shielding layer, and

wherein the light shielding pattern film has a Rd value of Equation 1 below of 0.4 to 0.8;

[Equation 1]

$$Rd = \frac{er_2}{er_1}$$

where in the Equation 1, the er_1 value is an etching rate of the first light shielding layer measured by etching with argon gas, and

the er_2 value is an etching rate of the second light shielding layer measured by etching with argon gas, and

wherein the Do value of Equation 2 below of the light shielding film is less than 0.05;

[Equation 2]

$$Do = Bo - Po$$

where in the Equation 2, the Bo value is an optical density of the light shielding film for a light with a wavelength of 193 nm, and

when a light shielding pattern film formed by patterning the light shielding film is observed at an upper surface, the Po value is an optical density for a light with a wavelength of 193 nm of a measuring area corresponded to an area from an edge of the light shielding pattern

film, to a position spaced apart by 4 mm from the edge in inner side direction of the light shielding pattern film.